

Jerzy Kanicki

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

273
papers

6,396
citations

44
h-index

68
g-index

311
ext. papers

6,881
ext. citations

2.8
avg, IF

5.61
L-index

#	Paper	IF	Citations
273	Enhancing Repetitive Uniaxial Mechanical Bending Endurance at $R = 2\%$ mm Using an Organic Trench Structure in Foldable Low Temperature Poly-Si Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 913-916	4.4	9
272	Study of ionically conducting nanocomposites for reflective electrochromic devices. <i>Electrochimica Acta</i> , 2019 , 301, 174-182	6.7	9
271	Enhancing Repetitive Uniaxial Mechanical Bending Endurance at $R = 2\%$ mm Using an Organic Trench Structure in Foldable Low Temperature Poly-Si Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2019 , 1-1	4.4	
270	Cascaded systems analysis of a-Se/a-Si and a-InGaZnO TFT passive and active pixel sensors for tomosynthesis. <i>Physics in Medicine and Biology</i> , 2019 , 64, 025012	3.8	4
269	Novel Top-Anode OLED/a-IGZO TFTs Pixel Circuit for 8K4K AM-OLEDs. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 436-444	2.9	12
268	Photoluminescence Study of Amorphous InGaZnO Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 1258-1261	2.9	1
267	Gellan gum/D,L-lysine-bis(2-aminopropyl)-polyethylene glycol hydrogel for controlled fertilizer release. <i>Journal of Applied Polymer Science</i> , 2018 , 135, 45636	2.9	6
266	Physical origin of the non-linearity in amorphous In-Ga-Zn-O thin-film transistor current-voltage characteristics. <i>Solid-State Electronics</i> , 2018 , 147, 51-57	1.7	1
265	High-performance PBT7-Th:PC70BM polymer photodiode with transferred charge blocking layers. <i>Organic Electronics</i> , 2018 , 62, 566-571	3.5	2
264	Study of current-mode active pixel sensor circuits using amorphous InSnZnO thin-film transistor for 50- μm pixel-pitch indirect X-ray imagers. <i>Solid-State Electronics</i> , 2017 , 131, 53-64	1.7	5
263	Task-Based Modeling of a 5k Ultra-High-Resolution Medical Imaging System for Digital Breast Tomosynthesis. <i>IEEE Transactions on Medical Imaging</i> , 2017 , 36, 1820-1831	11.7	1
262	Bilayer Interdiffused Heterojunction Organic Photodiodes Fabricated by Double Transfer Stamping. <i>Advanced Optical Materials</i> , 2017 , 5, 1600784	8.1	16
261	3D Printed Masks and Transfer Stamping Process to Enable the Fabrication of the Hemispherical Organic Photodiodes. <i>Advanced Materials Technologies</i> , 2017 , 2, 1700090	6.8	3
260	DNA-DODA-based polymer electrolytes for dye sensitized solar cells. <i>Molecular Crystals and Liquid Crystals</i> , 2017 , 655, 131-141	0.5	
259	DC sputtered amorphous In ₃ Sn ₂ ZnO thin-film transistors: Electrical properties and stability. <i>Solid-State Electronics</i> , 2016 , 116, 22-29	1.7	35
258	Response to "Comment on 'Large area CMOS active pixel sensor x-ray imager for digital breast tomosynthesis: Analysis, modeling, and characterization' " [Med. Phys. 43, 1578-1579 (2016)]. <i>Medical Physics</i> , 2016 , 43, 6210	4.4	
257	. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 4802-4810	2.9	11

256	Half-Corbino short-channel amorphous InGaZnO thin-film transistors with a-SiO _x or a-SiO _x /a-SiN _x passivation layers. <i>Solid-State Electronics</i> , 2016 , 120, 25-31	1.7	12
255	Influence of DNA and DNA-PEDOT: PSS on dye sensitized solar cell performance. <i>Molecular Crystals and Liquid Crystals</i> , 2016 , 627, 38-48	0.5	10
254	Comparison of composition and atomic structure of amorphous indium gallium zinc oxide thin film transistor before and after positive bias temperature stress by transmission electron microscopy. <i>Semiconductor Science and Technology</i> , 2015 , 30, 055008	1.8	3
253	Dynamic Response of a-InGaZnO and Amorphous Silicon Thin-Film Transistors for Ultra-High Definition Active-Matrix Liquid Crystal Displays. <i>Journal of Display Technology</i> , 2015 , 11, 471-479		18
252	Top illuminated organic photodetectors with dielectric/metal/dielectric transparent anode. <i>Organic Electronics</i> , 2015 , 20, 103-111	3.5	24
251	Short channel amorphous InGaZnO thin-film transistor arrays for ultra-high definition active matrix liquid crystal displays: Electrical properties and stability. <i>Solid-State Electronics</i> , 2015 , 111, 67-75	1.7	21
250	Electrochromic device with Prussian blue and HPC-based electrolyte. <i>Electrochimica Acta</i> , 2015 , 182, 878-883	6.7	13
249	50 μ m pixel pitch wafer-scale CMOS active pixel sensor x-ray detector for digital breast tomosynthesis. <i>Physics in Medicine and Biology</i> , 2015 , 60, 8977-9001	3.8	22
248	Large area CMOS active pixel sensor x-ray imager for digital breast tomosynthesis: Analysis, modeling, and characterization. <i>Medical Physics</i> , 2015 , 42, 6294-308	4.4	36
247	Density of states of short channel amorphous InGaZnO thin-film transistor arrays fabricated using manufacturable processes. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 051101	1.4	6
246	Electrical Instability of Double-Gate a-IGZO TFTs With Metal Source/Drain Recessed Electrodes. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 1109-1115	2.9	19
245	AC Bias-Temperature Stability of a-InGaZnO Thin-Film Transistors With Metal Source/Drain Recessed Electrodes. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 806-812	2.9	8
244	Density of states of amorphous In-Ga-Zn-O from electrical and optical characterization. <i>Journal of Applied Physics</i> , 2014 , 116, 154505	2.5	44
243	P-25: Top Gate Amorphous InGaZnO Thin Film Transistors Fabricated on Soda-Lime-Silica Glass Substrates. <i>Digest of Technical Papers SID International Symposium</i> , 2014 , 45, 1035-1038	0.5	2
242	An a-InGaZnO TFT Pixel Circuit Compensating Threshold Voltage and Mobility Variations in AMOLEDs. <i>Journal of Display Technology</i> , 2014 , 10, 402-406		16
241	Two-Dimensional Numerical Simulation of Bottom-Gate and Dual-Gate Amorphous In-Ga-Zn-O MESFETs. <i>IEEE Electron Device Letters</i> , 2014 , 35, 75-77	4.4	12
240	Amorphous In-Ga-Zn-O thin-film transistor active pixel sensor x-ray imager for digital breast tomosynthesis. <i>Medical Physics</i> , 2014 , 41, 091902	4.4	36
239	Impedance Analysis of Gellan Gum - Poly(vinyl pyrrolidone) Membranes. <i>Molecular Crystals and Liquid Crystals</i> , 2014 , 604, 84-95	0.5	4

238	Oxygen flow effects on electrical properties, stability, and density of states of amorphous InGaZnO thin-film transistors. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 121101	1.4	22
237	Properties of Electrodeposited WO ₃ Thin Films. <i>Molecular Crystals and Liquid Crystals</i> , 2014 , 604, 71-83	0.5	15
236	High Efficiency Cu(In,Ga)Se ₂ Flexible Solar Cells Fabricated by Roll-to-Roll Metallic Precursor Co-sputtering Method. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 092302	1.4	12
235	Dynamic response of amorphous In-Ga-Zn-O thin-film transistors for 8K flat-panel display 2013 ,		2
234	Scaling of Coplanar Homo Junction Amorphous InGaZnO Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 03BB05	1.4	6
233	16.3: AC and DC Bias-Temperature Stability of Coplanar Homo Junction a-InGaZnO Thin-Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2013 , 44, 174-177	0.5	3
232	High performance amorphous metal-oxide semiconductors thin-film passive and active pixel sensors 2013 ,		4
231	Solution-processed zinc tetrabenzoporphyrin thin-films and transistors. <i>Thin Solid Films</i> , 2012 , 520, 4031-4035	14	
230	Amorphous InGaZnO Dual-Gate TFTs: Current-Voltage Characteristics and Electrical Stress Instabilities. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 1928-1935	2.9	40
229	P-14: a-IGZO TFT Based Pixel Circuits for AM-OLED Displays. <i>Digest of Technical Papers SID International Symposium</i> , 2012 , 43, 1097-1100	0.5	3
228	Ab initio electronic structure calculations of solid, solution-processed metallotetrabenzoporphyrins. <i>Journal of Applied Physics</i> , 2012 , 111, 073709	2.5	3
227	P-11: Electrical Properties and Stability of Dual-Gate Coplanar Homo Junction Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistor. <i>Digest of Technical Papers SID International Symposium</i> , 2011 , 42, 1136-1139	0.5	6
226	Electrical Instability of the a-Si:H TFTs Fabricated by Maskless Laser-Write Lithography on a Spherical Surface. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 160-164	2.9	4
225	Electrical Properties and Stability of Dual-Gate Coplanar Homo Junction DC Sputtered Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistors and Its Application to AM-OLEDs. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 4344-4353	2.9	60
224	Back channel etch chemistry of advanced a-Si:H TFTs. <i>Microelectronic Engineering</i> , 2011 , 88, 207-212	2.5	4
223	Analyte selective response in solution-deposited tetrabenzoporphyrin thin-film field-effect transistor sensors. <i>Sensors and Actuators B: Chemical</i> , 2011 , 158, 333-339	8.5	19
222	Electrical Stability of Power Efficient Half Corbino Hydrogenated Amorphous Silicon Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 120203	1.4	
221	Crystalline InGaZnO Density of States and Energy Band Structure Calculation Using Density Function Theory. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 091102	1.4	11

220	Asymmetric Electrical Properties of Half Corbino Hydrogenated Amorphous Silicon Thin-Film Transistor and Its Applications to Flat Panel Displays. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 074203	1.4	3
219	Asymmetric Electrical Properties of Half Corbino Hydrogenated Amorphous Silicon Thin-Film Transistor and Its Applications to Flat Panel Displays. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 074203	1.4	6
218	Crystalline InGaZnO Density of States and Energy Band Structure Calculation Using Density Function Theory. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 091102	1.4	22
217	Electrical Stability of Power Efficient Half Corbino Hydrogenated Amorphous Silicon Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 120203	1.4	2
216	Low frequency noise in long channel amorphous InGaZnO thin film transistors. <i>Journal of Applied Physics</i> , 2010 , 108, 074518	2.5	60
215	Electrical Stability of Hexagonal a-Si:H TFTs. <i>IEEE Electron Device Letters</i> , 2010 , 31, 53-55	4.4	3
214	Surface potential study of amorphous InGaZnO thin film transistors. <i>Journal of Applied Physics</i> , 2010 , 108, 114508	2.5	11
213	Photogalvanic Cells. 5. Oxidation Photocurrents of Triphenylmethane Dyes at the SnO ₂ Bubbling Gas Electrode. <i>Bulletin Des Sociétés Chimiques Belges</i> , 2010 , 87, 849-856		6
212	Hemispherical thin-film transistor passive pixel sensors. <i>Sensors and Actuators A: Physical</i> , 2010 , 158, 280-283	3.9	8
211	A maskless laser-write lithography processing of thin-film transistors on a hemispherical surface. <i>Microelectronic Engineering</i> , 2010 , 87, 83-87	2.5	20
210	Two-dimensional numerical simulation of radio frequency sputter amorphous InGaZnO thin-film transistors. <i>Journal of Applied Physics</i> , 2009 , 106, 084511	2.5	193
209	Asymmetric electrical properties of fork a-Si:H thin-film transistor and its application to flat panel displays. <i>Journal of Applied Physics</i> , 2009 , 105, 124522	2.5	17
208	Amorphous InGaZnO Thin Film Transistor Current-Scaling Pixel Electrode Circuit for Active-Matrix Organic Light-Emitting Displays. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 03B025	1.4	20
207	Density of States of a-InGaZnO From Temperature-Dependent Field-Effect Studies. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 1177-1183	2.9	136
206	Electrical Instability of RF Sputter Amorphous In-Ga-Zn-O Thin-Film Transistors. <i>Journal of Display Technology</i> , 2009 , 5, 452-461		89
205	P-11: DC/AC Electrical Instability of R.F. Sputter Amorphous In-Ga-Zn-O TFTs. <i>Digest of Technical Papers SID International Symposium</i> , 2009 , 40, 1117	0.5	13
204	P-14: AM-OLED Pixel Circuits Based on a-InGaZnO Thin Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2009 , 40, 1128	0.5	9
203	Hexagonal a-Si:H TFTs: A New Advanced Technology for Flat-Panel Displays. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 329-336	2.9	13

202	Advanced Amorphous Silicon Thin-Film Transistors for AM-OLEDs: Electrical Performance and Stability. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 1621-1629	2.9	17
201	Dynamic Response of Normal and Corbino a-Si:H TFTs for AM-OLEDs. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 2338-2347	2.9	12
200	Study of the Density of States of a-InGaZnO Using Field-Effect Technique 2008 ,		3
199	Photofield-effect in amorphous In-Ga-Zn-O (a-IGZO) thin-film transistors. <i>Journal of Information Display</i> , 2008 , 9, 21-29	4.1	82
198	Advanced Multilayer Amorphous Silicon Thin-Film Transistor Structure: Film Thickness Effect on Its Electrical Performance and Contact Resistance. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 3362-3367 ^{1.4}		13
197	P-13: Photosensitivity of Amorphous IGZO TFTs for Active-Matrix Flat-Panel Displays. <i>Digest of Technical Papers SID International Symposium</i> , 2008 , 39, 1215	0.5	46
196	Asymmetric Electrical Properties of Corbino a-Si:H TFT and Concepts of Its Application to Flat Panel Displays. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 654-662	2.9	23
195	Current-Scaling a-Si:H TFT Pixel-Electrode Circuit for AM-OLEDs: Electrical Properties and Stability. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 2403-2410	2.9	14
194	Novel Current-Scaling Current-Mirror Hydrogenated Amorphous Silicon Thin-Film Transistor Pixel Electrode Circuit with Cascade Capacitor for Active-Matrix Organic Light-Emitting Devices. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 1343-1349	1.4	12
193	Absolute photoluminescence quantum efficiency measurement of light-emitting thin films. <i>Review of Scientific Instruments</i> , 2007 , 78, 096101	1.7	34
192	Polycrystalline tetrabenzoporphyrin organic field-effect transistors with nanostructured channels. <i>Applied Physics Letters</i> , 2007 , 90, 233107	3.4	34
191	Solution-processed polycrystalline copper tetrabenzoporphyrin thin-film transistors. <i>Synthetic Metals</i> , 2007 , 157, 190-197	3.6	51
190	Solution-processed nickel tetrabenzoporphyrin thin-film transistors. <i>Journal of Applied Physics</i> , 2006 , 100, 034502	2.5	58
189	White LED based on polyfluorene Co-polymers blend on plastic substrate. <i>IEEE Transactions on Electron Devices</i> , 2006 , 53, 427-434	2.9	10
188	70.3: Current-Scaling a-Si:H TFT Pixel Electrode Circuit for AM-OLEDs. <i>Digest of Technical Papers SID International Symposium</i> , 2006 , 37, 1968	0.5	
187	Poly(fluorene-oxadiazole) copolymer-based light-emitting devices on a plastic substrate. <i>Synthetic Metals</i> , 2005 , 155, 1-10	3.6	12
186	P-143: A Novel Current-Scaling a-Si:H TFTs Pixel Electrode Circuit for Active-Matrix Organic Light-Emitting Displays. <i>Digest of Technical Papers SID International Symposium</i> , 2005 , 36, 846	0.5	3
185	A novel current-scaling a-Si:H TFTs pixel electrode circuit for AM-OLEDs. <i>IEEE Transactions on Electron Devices</i> , 2005 , 52, 1123-1131	2.9	28

184	Electrical properties of staggered electrode, solution-processed, polycrystalline tetrabenzoporphyrin field-effect transistors. <i>IEEE Transactions on Electron Devices</i> , 2005 , 52, 1497-1503	2.9	24
183	Field-effect mobility of polycrystalline tetrabenzoporphyrin thin-film transistors. <i>Journal of Applied Physics</i> , 2005 , 98, 014503	2.5	79
182	Methanofullerene-coated tetrabenzoporphyrin organic field-effect transistors. <i>Applied Physics Letters</i> , 2005 , 87, 173506	3.4	12
181	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2004 , 10, 37-44	3.8	8
180	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2004 , 10, 16-25	3.8	10
179	Organic polymer thin-film transistor photosensors. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2004 , 10, 840-848	3.8	72
178	Opto-electronic properties of poly (fluorene) co-polymer red light-emitting devices on flexible plastic substrate. <i>IEEE Transactions on Electron Devices</i> , 2004 , 51, 1562-1569	2.9	15
177	Thin-film organic polymer phototransistors. <i>IEEE Transactions on Electron Devices</i> , 2004 , 51, 877-885	2.9	231
176	Transparent flexible plastic substrates for organic light-emitting devices. <i>Journal of Electronic Materials</i> , 2004 , 33, 312-320	1.9	32
175	Field-Effect Mobility of Organic Polymer Thin-Film Transistors. <i>Chemistry of Materials</i> , 2004 , 16, 4699-4704	3.6	41
174	Structural ordering and enhanced carrier mobility in organic polymer thin film transistors. <i>Synthetic Metals</i> , 2004 , 146, 181-185	3.6	96
173	Electrical Behavior of Organic Transistors and Circuits 2004 , 347-524		3
172	Contact Resistance in Schottky Contact Gated-Four-Probe a-Si Thin-Film Transistor. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, L907-L909	1.4	8
171	Monte Carlo modeling of organic polymer light-emitting devices on flexible plastic substrates 2003 , 4800, 156		7
170	Structural ordering in F8T2 polyfluorene thin film transistors 2003 , 5217, 35		12
169	Influence of gate dielectrics on electrical properties of F8T2 polyfluorene thin film transistors 2003 , ,		11
168	25.1: Luminance Probes for Contrast Measurements in Medical Displays. <i>Digest of Technical Papers SID International Symposium</i> , 2003 , 34, 928	0.5	2
167	4.5: 200 dpi 4-a-Si:H TFTs Current-Driven AM-PLEDs. <i>Digest of Technical Papers SID International Symposium</i> , 2003 , 34, 22	0.5	

166	Organic polymer thin film phototransistors 2003 ,		1
165	4.4: 200 dpi 3-a-Si:H TFTs Voltage-Driven AM-PLEDs. <i>Digest of Technical Papers SID International Symposium</i> , 2003 , 34, 18	0.5	2
164	Hydrogenated Amorphous Silicon Thin-Film Transistors 2003 ,		6
163	Source / drain contacts in organic polymer thin film transistors. <i>Materials Research Society Symposia Proceedings</i> , 2003 , 771, 621		1
162	Amorphous silicon TFT-based active-matrix organic polymer LEDs. <i>IEEE Electron Device Letters</i> , 2003 , 24, 451-453	4.4	8
161	Angular dependence of the luminance and contrast in medical monochrome liquid crystal displays. <i>Medical Physics</i> , 2003 , 30, 2602-13	4.4	32
160	Integrating sphere charge coupled device-based measurement method for organic light-emitting devices. <i>Review of Scientific Instruments</i> , 2003 , 74, 3572-3575	1.7	11
159	Optoelectrical properties of four amorphous silicon thin-film transistors 200 dpi active-matrix organic polymer light-emitting display. <i>Applied Physics Letters</i> , 2003 , 83, 3233-3235	3.4	12
158	Effect of Illumination on Organic Polymer Thin-Film Transistors. <i>Materials Research Society Symposia Proceedings</i> , 2003 , 771, 10171		3
157	Gate-planarized organic polymer thin film transistors. <i>Journal of Electronic Materials</i> , 2002 , 31, 512-519	1.9	7
156	Accurate small-spot luminance measurements. <i>Displays</i> , 2002 , 23, 177-182	3.4	12
155	Air-stable organic polymer red light-emitting devices on flexible plastic substrates 2002 ,		4
154	High-resolution organic polymer light-emitting pixels fabricated by imprinting technique. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002 , 20, 2877		52
153	Characterization of a high-quality monochrome AM-LCD monitor for digital radiology 2002 ,		7
152	P-102: Amorphous Silicon Thin-Film Transistors-based Active-Matrix Organic Light-Emitting Displays. <i>Digest of Technical Papers SID International Symposium</i> , 2002 , 33, 614	0.5	1
151	P-103: Novel Poly-Si TFT Pixel Electrode Circuits and Current Programmed Active-Matrix Driving Methods for AM-OLEDs. <i>Digest of Technical Papers SID International Symposium</i> , 2002 , 33, 618	0.5	9
150	Amorphous silicon thin-film transistor-based active-matrix organic light-emitting displays for medical imaging 2002 ,		4
149	Materials and device structures for high-performance poly OLEDs on flexible plastic substrates 2001 , 4105, 356		3

148	Characterization of crosstalk in high-resolution active matrix liquid crystal displays for medical imaging 2001 ,		2
147	Polyfluorene light-emitting devices on flexible plastic substrates 2001 ,		1
146	Improved a-Si:H TFT pixel electrode circuits for active-matrix organic light emitting displays. <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 1322-1325	2.9	75
145	Four-Thin Film Transistor Pixel Electrode Circuits for Active-Matrix Organic Light-Emitting Displays. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, 1199-1208	1.4	46
144	Monte Carlo analysis of the spectral photon emission and extraction efficiency of organic light-emitting devices. <i>Journal of Applied Physics</i> , 2001 , 90, 1827-1830	2.5	26
143	Influence of the Amorphous Silicon Thickness on Top Gate Thin-Film Transistor Electrical Performances. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, 530-537	1.4	65
142	Advanced amorphous silicon thin film transistor active-matrix organic light-emitting displays design for medical imaging 2001 ,		2
141	Interference fringe-free transmission spectroscopy of amorphous thin films. <i>Journal of Applied Physics</i> , 2000 , 88, 5764-5771	2.5	15
140	High-efficiency organic polymer light-emitting heterostructure devices on flexible plastic substrates. <i>Applied Physics Letters</i> , 2000 , 76, 661-663	3.4	93
139	Light output measurements of the organic light-emitting devices. <i>Review of Scientific Instruments</i> , 2000 , 71, 2104-2107	1.7	14
138	Current-source a-Si:H thin-film transistor circuit for active-matrix organic light-emitting displays. <i>IEEE Electron Device Letters</i> , 2000 , 21, 590-592	4.4	73
137	Two-Dimensional Numerical Simulation of Solid-Phase-Crystallized Polysilicon Thin-Film Transistor Characteristics. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, 2251-2255	1.4	37
136	Ultraviolet-light Induced Liquid-Crystal Alignment on Polyimide Films. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, 5996-6004	1.4	20
135	High-fidelity electronic display of digital radiographs. <i>Radiographics</i> , 1999 , 19, 1653-69	5.4	45
134	Electrical characteristics of new LDD poly-Si TFT structure tolerant to process misalignment. <i>IEEE Electron Device Letters</i> , 1999 , 20, 335-337	4.4	13
133	Microstructure characterization of amorphous thin solid films in a fringe-free environment. <i>Journal of Applied Physics</i> , 1999 , 85, 388-396	2.5	5
132	High performance organic polymer light-emitting heterostructure devices. <i>Applied Physics Letters</i> , 1999 , 74, 2265-2267	3.4	112
131	Method of collecting pure vibrational absorption spectra of amorphous thin films. <i>Thin Solid Films</i> , 1999 , 349, 283-288	2.2	2

130	Thin film transistors in low temperature as-deposited and reduced-crystallization-time polysilicon on 665°C strain point glass substrates. <i>Thin Solid Films</i> , 1999 , 338, 281-285	2.2	10
129	Planarized copper gate hydrogenated amorphous-silicon thin-film transistors for AM-LCDs. <i>IEEE Electron Device Letters</i> , 1999 , 20, 129-131	4.4	22
128	Tuning Optical and Electronic Properties of Bithiazole Containing Polymers by N-Methylation. <i>Macromolecules</i> , 1999 , 32, 2484-2489	5.5	19
127	A High-Voltage Hydrogenated Amorphous Silicon Thin-Film Transistor for Reflective Active-Matrix Cholesteric LCD. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 558, 125		1
126	Small Spot Contrast Measurements in High Performance Displays. <i>Digest of Technical Papers SID International Symposium</i> , 1999 , 30, 516	0.5	1
125	Schottky-contact gated-four-probe a-Si:H TFT structure: a new structure to investigate the electrical instability of a-Si:H TFT. <i>IEEE Electron Device Letters</i> , 1998 , 19, 382-384	4.4	10
124	Synthesis and Characterization of Conjugated, n-Dopable, Bithiazole-Containing Polymers. <i>Chemistry of Materials</i> , 1998 , 10, 1713-1719	9.6	48
123	Observation of incident angle dependent phonon absorption in hydrogenated amorphous silicon nitride thin films. <i>Applied Physics Letters</i> , 1998 , 73, 3866-3868	3.4	14
122	Investigation of intrinsic channel characteristics of hydrogenated amorphous silicon thin-film transistors by gated-four-probe structure. <i>Applied Physics Letters</i> , 1998 , 72, 2874-2876	3.4	22
121	Electrical Instability of Hydrogenated Amorphous Silicon Thin-Film Transistors for Active-Matrix Liquid-Crystal Displays. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, 4704-4710	1.4	91
120	Top-Gate Staggered Amorphous Silicon Thin-Film Transistors: Series Resistance and Nitride Thickness Effects. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, 5914-5920	1.4	76
119	Effect of secondary radiations on the performance of digital radiographic detectors 1998 ,		7
118	High-performance top-gate a-Si:H TFTs for AMLCDs. <i>Digest of Technical Papers SID International Symposium</i> , 1998 , 29, 383	0.5	2
117	Planarization technology of a-Si:H TFTs for AM LCDs 1998 , 3421, 170		9
116	P-64: UV-Light-Modified Polyimide Films for Liquid-Crystal Alignment. <i>Digest of Technical Papers SID International Symposium</i> , 1998 , 29, 722	0.5	3
115	Full-Color Light-Emitting Devices Based on π and σ Conjugated Polymer Materials. <i>Digest of Technical Papers SID International Symposium</i> , 1998 , 29, 663	0.5	2
114	Longitudinal Vibrational Absorption Modes of Hydrogenated Amorphous Silicon Nitride Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 507, 535		
113	Effects of Ultraviolet-Light on Polyimide Films for Liquid Crystal Alignment. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 508, 229		

112	Aluminum Gate Metallization for AMLCDs. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 471, 111		3
111	Electrical Characteristics of New LDD Poly-Si TFT with MIS-Alignment Tolerant Structure for AMLCDs. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 471, 137		
110	Electrical and Optical Properties of Low Dielectric Constant Planarization Polymer for High-Aperture-Ratio a-Si:H TFT-LCDs. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 471, 27		4
109	Gated-four-probe a-Si:H TFT structure: a new technique to measure the intrinsic performance of a-Si:H TFT. <i>IEEE Electron Device Letters</i> , 1997 , 18, 340-342	4.4	35
108	Characterization and stability of light-emitting diodes based on poly(bithiazole)'s. <i>IEEE Transactions on Electron Devices</i> , 1997 , 44, 1282-1288	2.9	14
107	ITO surface ball formation induced by atomic hydrogen in PECVD and HW-CVD tools. <i>Thin Solid Films</i> , 1997 , 304, 123-129	2.2	31
106	Creation and Properties of Nitrogen Dangling Bond Defects in Silicon Nitride Thin Films. <i>Journal of the Electrochemical Society</i> , 1996 , 143, 3685-3691	3.9	24
105	Direct determination of the quadratic electro-optic coefficient in an a-Si:H based waveguide. <i>Journal of Non-Crystalline Solids</i> , 1996 , 198-200, 107-110	3.9	7
104	Study of sub-bandgap photo-induced absorption in a-Si:H using excitation spectroscopy in a waveguide configuration. <i>Journal of Non-Crystalline Solids</i> , 1996 , 198-200, 259-262	3.9	4
103	High field-effect-mobility a-Si:H TFT based on high deposition-rate PECVD materials. <i>IEEE Electron Device Letters</i> , 1996 , 17, 437-439	4.4	36
102	Atomic Hydrogen Effects on the Optical and Electrical Properties of Transparent Conducting Oxides For a-Si:H TFT-LCDs. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 424, 347		18
101	High-Rate Deposited Amorphous Silicon Nitride for the Hydrogenated Amorphous Silicon Thin-Film Transistor Structures. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 424, 43		7
100	Poly(bithiazole)s: A New Class of Conjugated Polymers for Polymer-Based Light-Emitting Diodes. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 424, 495		4
99	Influence of the Density of States and Series Resistance on the Field-Effect Activation Energy in a-Si:H TFT. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 424, 77		8
98	Patterning of transparent conducting oxide thin films by wet etching for a-Si:H TFT-LCDs. <i>Journal of Electronic Materials</i> , 1996 , 25, 1806-1817	1.9	39
97	Paramagnetic point defects in silicon nitride and silicon oxynitride thin films on silicon. <i>Colloids and Surfaces A: Physicochemical and Engineering Aspects</i> , 1996 , 115, 311-317	5.1	14
96	Selective deposition of polycrystalline silicon thin films at low temperature by hot-wire chemical vapor deposition. <i>Applied Physics Letters</i> , 1996 , 68, 2681-2683	3.4	11
95	Ultraviolet light induced changes in polyimide liquid-crystal alignment films. <i>Journal of Applied Physics</i> , 1996 , 80, 5028-5034	2.5	67

94	Ultraviolet light induced annihilation of silicon dangling bonds in hydrogenated amorphous silicon nitride films. <i>Journal of Applied Physics</i> , 1995 , 77, 5730-5735	2.5	12
93	Photoluminescence and electron spin resonance in nitrogen-rich amorphous silicon nitride. <i>Journal of Non-Crystalline Solids</i> , 1995 , 182, 103-108	3.9	6
92	Nature of the Si and N dangling bonds in silicon nitride. <i>Journal of Non-Crystalline Solids</i> , 1995 , 187, 297-300	3.9	37
91	Low Temperature Deposition of Polycrystalline Silicon thin Films by Hot-Wire CVD. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 377, 69		7
90	Selective Deposition of Polycrystalline Silicon Thin Films by Hot-Wire CVD. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 403, 411		
89	Temperature dependence of the electron-spin resonance in nitrogen-rich amorphous silicon nitride. <i>Physical Review B</i> , 1994 , 49, 13420-13422	3.3	8
88	Photobleaching of PL and Temperature Dependence of ESR in Nitrogen-Rich Amorphous Silicon Nitride Films. <i>Materials Research Society Symposia Proceedings</i> , 1994 , 336, 619		
87	Defects in amorphous hydrogenated silicon nitride films. <i>Journal of Non-Crystalline Solids</i> , 1993 , 164-166, 1055-1060	3.9	17
86	Bias-stress-induced stretched-exponential time dependence of charge injection and trapping in amorphous thin-film transistors. <i>Applied Physics Letters</i> , 1993 , 62, 1286-1288	3.4	384
85	Si and N dangling bond creation in silicon nitride thin films. <i>Applied Physics Letters</i> , 1993 , 63, 2685-2687	3.4	59
84	Electron paramagnetic resonance investigation of charge trapping centers in amorphous silicon nitride films. <i>Journal of Applied Physics</i> , 1993 , 74, 4034-4046	2.5	89
83	Photocreation and photobleaching of a-Si N1.6:H/c-Si interface states studied by photocapacitance transient spectroscopy. <i>Physica B: Condensed Matter</i> , 1993 , 185, 542-545	2.8	
82	Optically Induced Nitrogen Dangling Bonds in Amorphous Hydrogenated Silicon Nitride Thin Films 1993 , 421-426		
81	Photocreation and photobleaching of a-Si N1.6:H/c-Si interface states studied by photocapacitance transient spectroscopy 1993 , 542-545		
80	Near-ir absorption in chemically vapor deposited a-SiNx:H films. <i>Physical Review B</i> , 1992 , 46, 15163-15168	3.3	7
79	Enhanced electro-optic effect in amorphous hydrogenated silicon based waveguides. <i>Applied Physics Letters</i> , 1992 , 61, 1664-1666	3.4	11
78	Charge trapping centers in N-rich silicon nitride thin films. <i>Applied Physics Letters</i> , 1992 , 61, 216-218	3.4	26
77	Optically Induced Paramagnetism in Amorphous Hydrogenated Silicon Nitride Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 242, 687		7

76	Structure, Characteristics, and the Application of Phosphorus Doped Hydrogenated Microcrystalline Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 242, 693		
75	Photoluminescence in Nitrogen-Rich a-SiNx:H. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 258, 661		7
74	Paramagnetic Nitrogen Defects in Silicon Nitride. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 284, 101		3
73	The Effect of UV Light on IR Absorption in Chemically Vapor Deposited a-SiNx:H Films. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 284, 89		
72	Performance of Polycrystalline Silicon Thin Film Transistors with Double Layer Gate Dielectric. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 284, 431		
71	Paramagnetic Point Defects in Amorphous Silicon Dioxide and Amorphous Silicon Nitride Thin Films: II .. <i>Journal of the Electrochemical Society</i> , 1992 , 139, 880-889	3.9	82
70	Some electrical properties of amorphous silicon/amorphous silicon nitride interfaces: Top nitride and bottom nitride configurations in MNS and TFT devices. <i>Journal of Applied Physics</i> , 1992 , 71, 5022-5032 ⁵	2.5	13
69	Investigations on the quality of polysilicon film-gate dielectric interface in polysilicon thin film transistors. <i>Thin Solid Films</i> , 1992 , 216, 137-141	2.2	13
68	Hydrogenation effects on polysilicon thin-film transistor structures. <i>IEEE Transactions on Electron Devices</i> , 1992 , 39, 2665	2.9	
67	Thermal Annealing of Light-Induced K Centers in Hydrogenated Amorphous Silicon Nitride. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 219, 129		2
66	Influence of the Gate Bias and Temperature on Positive Charge Generation in TFT Gate-Quality Amorphous Silicon Nitride Films. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 219, 363		3
65	Bias Stress Induced Instabilities in Amorphous Silicon Nitride / Crystalline Silicon and Amorphous Silicon Nitride / Amorphous Silicon Structures. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 219, 45		5
64	Structure, properties, and thermal stability of in situ phosphorus-doped hydrogenated microcrystalline silicon prepared by plasma-enhanced chemical vapor deposition. <i>Applied Physics Letters</i> , 1991 , 58, 1632-1634	3.4	5
63	Thermal annealing of light-induced metastable defects in hydrogenated amorphous silicon nitride. <i>Applied Physics Letters</i> , 1991 , 59, 1723-1725	3.4	44
62	Electrically neutral nitrogen dangling-bond defects in amorphous hydrogenated silicon nitride thin films. <i>Journal of Applied Physics</i> , 1991 , 70, 2220-2225	2.5	50
61	Threshold and saturation effects for photosignals in an amorphous silicon waveguide structure. <i>Applied Physics Letters</i> , 1991 , 59, 2660-2662	3.4	5
60	Low-temperature electron spin resonance investigations of silicon paramagnetic defects in silicon nitride. <i>Applied Physics Letters</i> , 1991 , 58, 2417-2419	3.4	7
59	Structural identification of the silicon and nitrogen dangling-bond centers in amorphous silicon nitride. <i>Journal of Applied Physics</i> , 1991 , 70, 346-354	2.5	71

58	Microscopic origin of the light-induced defects in hydrogenated nitrogen-rich amorphous silicon nitride films. <i>Journal of Non-Crystalline Solids</i> , 1991 , 137-138, 291-294	3.9	51
57	Determination of electron and hole mobilities in an a-Si:H from photo-electric effects in a waveguide structure. <i>Journal of Non-Crystalline Solids</i> , 1991 , 137-138, 455-458	3.9	2
56	Transient photocapacitance and capacitance studies of interface and bulk states in metal / a-SiN _{1.6} :H / a-Si:H / c-Si devices. <i>Journal of Non-Crystalline Solids</i> , 1991 , 137-138, 1051-1054	3.9	3
55	Performance of thin hydrogenated amorphous silicon thin-film transistors. <i>Journal of Applied Physics</i> , 1991 , 69, 2339-2345	2.5	119
54	Energy level of the nitrogen dangling bond in amorphous silicon nitride. <i>Applied Physics Letters</i> , 1991 , 59, 1699-1701	3.4	42
53	Effect of Gate Dielectric on Performance of Polysilicon Thin Film Transistors. <i>Materials Research Society Symposia Proceedings</i> , 1990 , 182, 357		10
52	The Generation and Bleaching of Positive Charge in Gate-Quality Nitrogen-Rich Amorphous Silicon Nitride By Sub-Bandgap Illumination. <i>Materials Research Society Symposia Proceedings</i> , 1990 , 192, 731		3
51	Photobleaching of light-induced paramagnetic defects in amorphous silicon nitride films. <i>Applied Physics Letters</i> , 1990 , 57, 1995-1997	3.4	41
50	Evidence for a negative electron-electron correlation energy in the dominant deep trapping center in silicon nitride films. <i>Applied Physics Letters</i> , 1990 , 56, 1359-1361	3.4	51
49	Stretched exponential illumination time dependence of positive charge and spin generation in amorphous silicon nitride. <i>Applied Physics Letters</i> , 1990 , 57, 698-700	3.4	34
48	Photodarkening and bleaching in amorphous silicon nitride. <i>Applied Physics Letters</i> , 1990 , 57, 1378-1380	3.4	22
47	Bias stress-induced instabilities in amorphous silicon nitride/hydrogenated amorphous silicon structures: Is the barrier-induced defect creation model correct?. <i>Applied Physics Letters</i> , 1990 , 57, 1197-1199	3.4	66
46	Direct observation of the silicon nitride on amorphous silicon interface states. <i>Applied Physics Letters</i> , 1990 , 56, 940-942	3.4	15
45	Properties of High Conductivity Phosphorous Doped Hydrogenated Microcrystalline Silicon and Application in Thin Film Transistor Technology. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 149, 239		24
44	Stability of electrical properties of nitrogen-rich, silicon-rich, and stoichiometric silicon nitride films. <i>Journal of Applied Physics</i> , 1989 , 66, 2765-2767	2.5	41
43	Observation of multiple silicon dangling bond configurations in silicon nitride. <i>Applied Physics Letters</i> , 1989 , 54, 1043-1045	3.4	44
42	The nature of the dominant deep trap in amorphous silicon nitride films: Evidence for a negative correlation energy. <i>Applied Surface Science</i> , 1989 , 39, 392-405	6.7	57
41	Electron spin resonance study of metal-nitride-silicon structures: Observation of Si dangling bonds with different configurations and trapping properties in silicon nitride. <i>Applied Surface Science</i> , 1989 , 39, 412-419	6.7	7

40	Gate dielectric and contact effects in hydrogenated amorphous silicon-silicon nitride thin-film transistors. <i>Journal of Applied Physics</i> , 1989 , 65, 3951-3957	2.5	109
39	Light-induced effects in hydrogenated amorphous nitrogen-rich silicon nitride films. <i>Journal of Non-Crystalline Solids</i> , 1989 , 114, 612-614	3.9	11
38	. <i>IEEE Electron Device Letters</i> , 1989 , 10, 277-279	4.4	12
37	Investigation of the light-induced effects in nitrogen-rich silicon nitride films. <i>Applied Physics Letters</i> , 1989 , 55, 1112-1114	3.4	40
36	Spatial charge distribution in the plasma-enhanced chemical vapor deposited nitrogen-rich silicon nitride. <i>Applied Physics Letters</i> , 1989 , 54, 733-735	3.4	17
35	Properties and Application of Undoped Hydrogenated Microcrystalline Silicon Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 149, 173		5
34	Investigation of the Silicon Nitride on Hydrogenated Amorphous Silicon Interface. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 149, 729		7
33	Correlations Between Optical, Electrical, and Structural Properties of In-Situ Phosphorus-Doped Hydrogenated Microcrystalline Silicon - Effects of Rapid Thermal Annealing on Material Properties. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 164, 353		3
32	Electrically active point defects in amorphous silicon nitride: An illumination and charge injection study. <i>Journal of Applied Physics</i> , 1988 , 64, 3558-3563	2.5	151
31	Nature of the dominant deep trap in amorphous silicon nitride. <i>Physical Review B</i> , 1988 , 38, 8226-8229	3.3	79
30	Electron-spin-resonance study of defects in plasma-enhanced chemical vapor deposited silicon nitride. <i>Applied Physics Letters</i> , 1988 , 52, 445-447	3.4	52
29	Contact resistance to undoped and phosphorus-doped hydrogenated amorphous silicon films. <i>Applied Physics Letters</i> , 1988 , 53, 1943-1945	3.4	46
28	Temperature Dependent Characteristics of Hydrogenated Amorphous Silicon thin film Transistors. <i>Materials Research Society Symposia Proceedings</i> , 1988 , 118, 267		23
27	Role of Hydrogen in Silicon Nitride Films Prepared by Various Deposition Techniques. <i>Materials Research Society Symposia Proceedings</i> , 1988 , 118, 671		19
26	Electron Spin Resonance Spectroscopy Of Defects In Low Temperature Dielectric Films 1988 ,		2
25	Stable photoinduced paramagnetic defects in hydrogenated amorphous silicon nitride. <i>Applied Physics Letters</i> , 1987 , 51, 608-610	3.4	55
24	Metal / Hydrogenated Amorphous Silicon Interfaces. <i>Materials Research Society Symposia Proceedings</i> , 1987 , 95, 399		5
23	Chemical and Mechanical Properties of Hydrogenated Amorphous Silicon Nitride Films Deposited in Various PECVD Systems. <i>Materials Research Society Symposia Proceedings</i> , 1986 , 68, 167		9

22	Optical and Electrical Properties of Hydrogenated Amorphous Silicon Nitride Films Deposited in Various PECVD Systems. <i>Materials Research Society Symposia Proceedings</i> , 1986 , 68, 175		7
21	Ohmic and Quasi-Ohmic Contacts to Hydrogenated Amorphous Silicon Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 1986 , 70, 379		8
20	Minority Carrier Injection and Series Resistance Effects in Hydrogenated Amorphous Silicon Schottky Barrier Diodes. <i>Materials Research Society Symposia Proceedings</i> , 1985 , 49, 101		3
19	Far UV pulsed laser melting of silicon. <i>Applied Physics Letters</i> , 1985 , 46, 547-549	3.4	50
18	Optical, electrical and contact properties of homoCVD a-Si:H films. <i>Journal of Non-Crystalline Solids</i> , 1985 , 77-78, 789-792	3.9	5
17	Electrical and photovoltaic properties of trans-polyacetylene. <i>Journal Physics D: Applied Physics</i> , 1984 , 17, 805-817	3	11
16	Electrical and photovoltaic properties of metal contacts to trans-polyacetylene. <i>Thin Solid Films</i> , 1984 , 113, 1-14	2.2	10
15	Electrical and photovoltaic properties of Pb/trans- (CH) _x and Pb/[CH(AsF ₅) _y] _x schottky barriers. <i>Journal of Applied Polymer Science</i> , 1984 , 29, 619-627	2.9	6
14	Transport properties and defect states of a-Si:H grown by HOMOCVD. <i>Journal of Non-Crystalline Solids</i> , 1984 , 66, 51-58	3.9	6
13	Metal - Polyacetylene Schottky Barrier Diodes. <i>Molecular Crystals and Liquid Crystals</i> , 1984 , 105, 203-217	0.5	34
12	Photovoltaic properties of In/trans-polyacetylene/Electrodag+502 Schottky barrier cells. <i>Solar Cells</i> , 1983 , 9, 281-288		3
11	Photovoltaic and rectification properties of In/trans-(CH) _x /electrodag +502 schottky-barrier cells. <i>Molecular Crystals and Liquid Crystals</i> , 1982 , 83, 319-327		8
10	Photovoltaic properties of the poly-2-vinylpyridine iodine complex/SnO ₂ system. <i>Journal of Applied Polymer Science</i> , 1982 , 27, 1-9	2.9	14
9	Novel approach to the study of electrical conduction in bromine-doped polyacetylene. <i>Thin Solid Films</i> , 1982 , 92, 243-251	2.2	4
8	Organic Photovoltaic Materials: Polyacetylene 1982 , 562-567		
7	Electrical conductivity and infrared absorption of trans- polyacetylene in the presence of iodine. <i>Journal of the Chemical Society, Faraday Transactions 2</i> , 1981 , 77, 2157-2168		12
6	Junction formation between undoped polyacetylene and metals. <i>European Polymer Journal</i> , 1980 , 16, 677-678	5.2	9
5	Fingerprint imager based on a-Si:H active-matrix photo-diode arrays		4

4	Five-terminal amorphous silicon thin-film transistor structure	2
3	Hydrogenated amorphous-silicon thin-film transistor structure with buried field plate	3
2		1
1	An alternative transparent conducting oxide to ITO for the a-Si:H TFT-LCD applications	2